



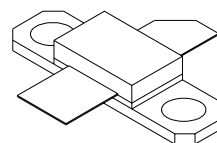
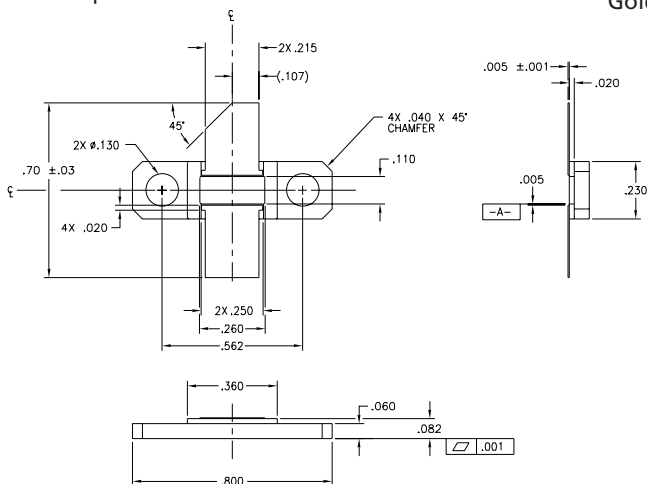
UPF2425

25W, 2.4GHz, 26.5V Broadband RF Power N-Channel Enhancement-Mode Lateral DMOS

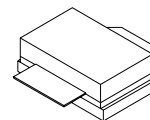
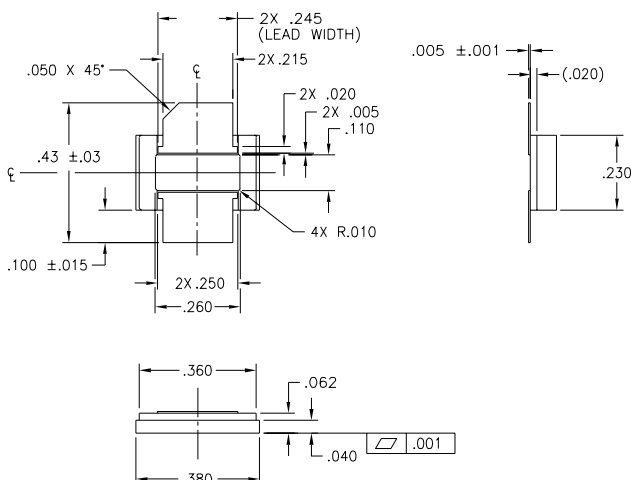
Description

This device is designed for base station applications operating at or near 2.4GHz. Rated with a minimum output power of 25W, it is ideal for CDMA, TDMA, GSM, FM, Single or Multi-Carrier Power Amplifiers in Class A or AB operation.

- Industry standard package.
- Low intermodulation distortion of -30dBc at 25W (PEP).
- Gold Metalization, Gold Bond Wires, Gold-Plated Packages.



Package Type 440095



Package Type 440134

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Maximum Ratings

Rating	Symbol	Value	Unit
Drain to Source Voltage, gate connected to source	V_{DSS}	65	Volts
Gate to Source Voltage	V_{GS}	± 20	Volts
Total Device Dissipation @ $T_{case} = 70^{\circ}C$ Derate above $70^{\circ}C$	P_D	65 0.5	Watts $W/^{\circ}C$
Storage Temperature Range	T_{STG}	-65 to +150	$^{\circ}C$
Operating Junction Temperature	T_J	200	$^{\circ}C$

Thermal Characteristics

Characteristics	Symbol	Maximum	Unit
Thermal Resistance, Junction to Case	Θ_{JC}	2.0	$^{\circ}C/W$

Electrical DC Characteristics ($T_C=25^{\circ}C$ unless otherwise specified)

Rating	Symbol	Min	Typ	Max	Unit
Drain to Source Voltage, gate connected to source ($V_{GS}=0$, $I_{DS}=1mA$)	BV_{DSS}	65	-	-	Volts
Drain to Source Leakage current ($V_{DS}=28V$, $V_{GS}=0$)	I_{DSS}	-	-	1.0	mA
Gate to Source Leakage current ($V_{GS}=20V$, $V_{DS}=0$)	I_{GSS}	-	-	1.0	μA
Threshold Voltage ($V_{DS}=10V$, $I_{DS}=1mA$)	V_{th}	2.0	3.5	5.0	Volts
Gate Quiescent Voltage ($V_{DS}=26V$, $I_{DS}=200mA$)	$V_{GS(on)}$	3.0	4.0	6.0	Volts
Drain to Source On Voltage ($V_{GS}=10V$, $I_{DS}=1A$)	$V_{DS(on)}$	-	0.28	-	Volts
Forward Transconductance ($V_{DS}=10V$, $I_D=5A$)	G_m	1.4	1.8	-	S

AC Characteristics ($T_C=25^{\circ}\text{C}$ unless otherwise specified)

Rating	Symbol	Min	Typ	Max	Unit
Output capacitance ($V_{DS}=26\text{V}$, $V_{GS}=0\text{V}$, freq= 1MHz)	C_{OSS}	-	26	-	pF
Feedback capacitance ($V_{DS}=26\text{V}$, $V_{GS}=0\text{V}$, freq= 1MHz)	C_{RSS}	-	1.2	-	pF

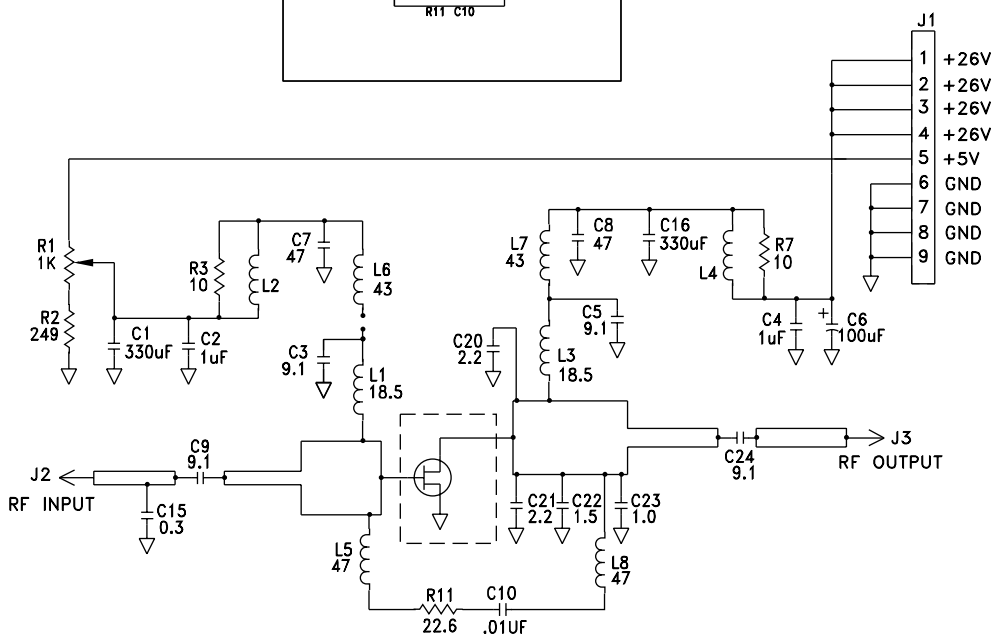
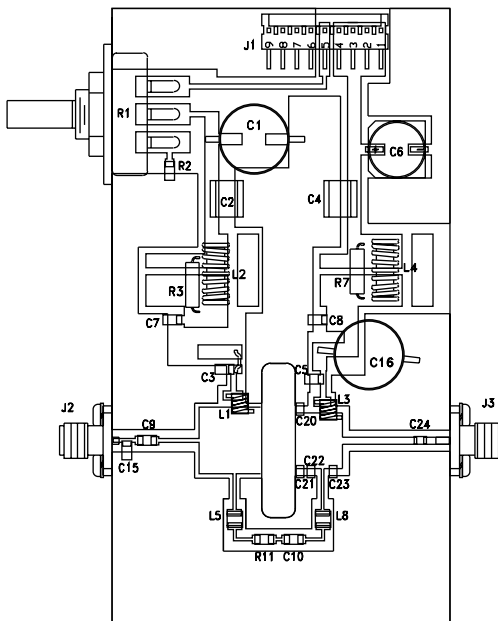
RF and Functional Tests ($T_C=25^{\circ}\text{C}$ unless otherwise specified, UltraRF Broadband Fixture)

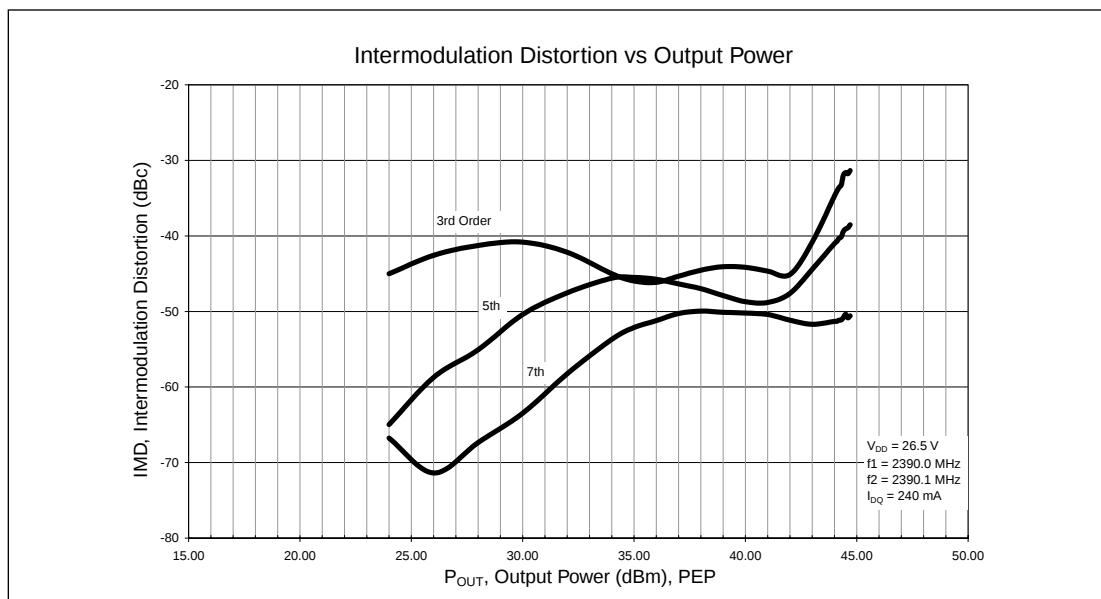
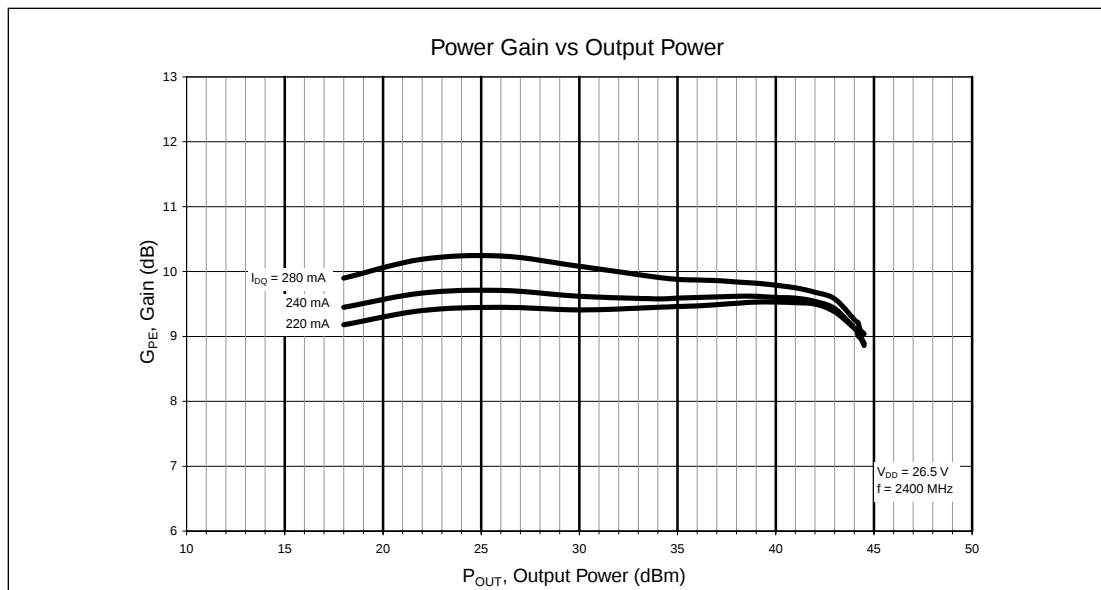
Rating	Symbol	Min	Typ	Max	Unit
Linear Power Gain, Single Tone ($V_{DS}=26.5\text{V}$, $I_{DQ}=240\text{mA}$, $P_{OUT}=5\text{W}$, $f=2400\text{ MHz}$)	G_{plin}	8.5	10.0	-	dB
Compressed Power Gain, Single Tone ($V_{DS}=26.5\text{V}$, $I_{DQ}=240\text{mA}$, $P_{OUT}=25\text{W}$, $f=2400\text{ MHz}$)	G_{ps}	8.0	9.3	-	dB
Drain Efficiency, Single Tone ($V_{DS}=26.5\text{V}$, $I_{DQ}=240\text{mA}$, $P_{OUT}=25\text{W}$, $f=2400\text{ MHz}$)	η	35	40	-	%
Intermodulation Distortion, Two Tone ($V_{DS}=26.5\text{V}$, $I_{DQ}=225\text{mA}$, $P_{OUT}=25\text{W PEP}$ $f1=2390\text{ MHz}$, $f2=2390.1\text{MHz}$)	IMD	-	-32	-30	dBc
Load Mismatch Tolerance ($V_{DS}=26.5\text{V}$, $I_{DQ}=225\text{mA}$, $P_{OUT}=25\text{W}$, $f=2400\text{ MHz}$)	VSWR	10:1	-	-	

CAUTION - MOS Devices are susceptible to damage from ElectroStatic Discharge (ESD). Appropriate precautions in handling, packaging and testing MOS devices must be observed.

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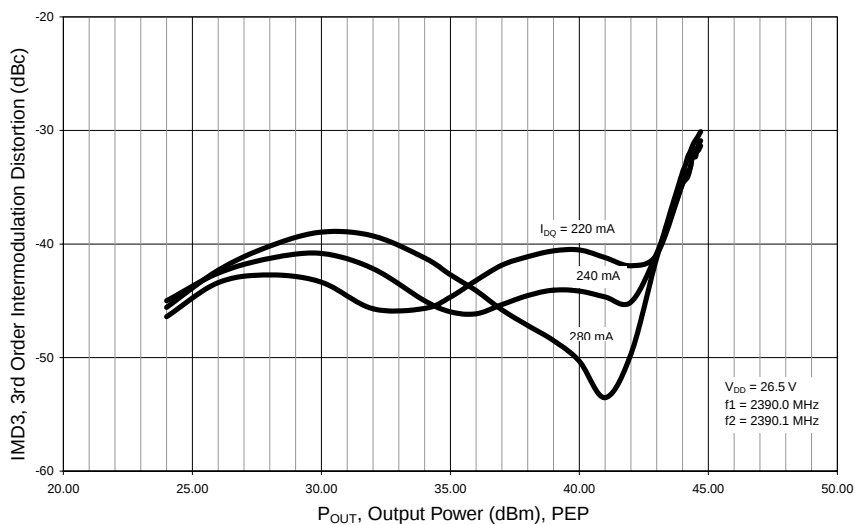
Fixture Drawings



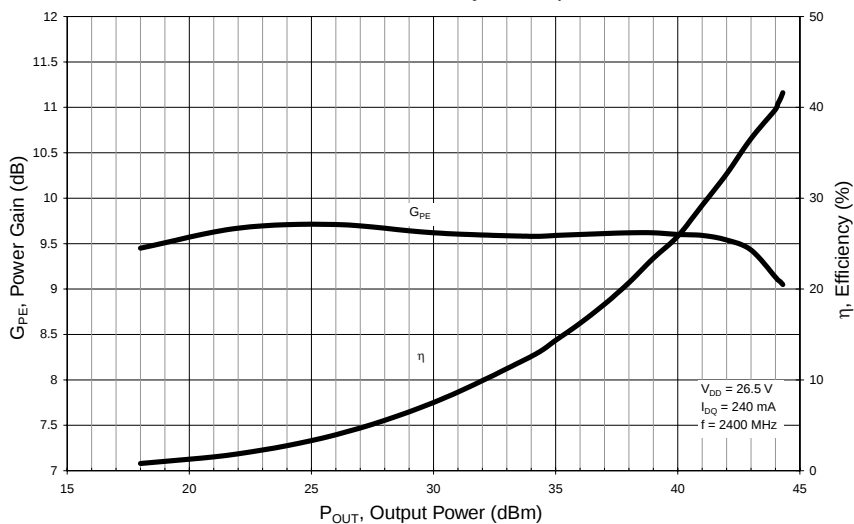


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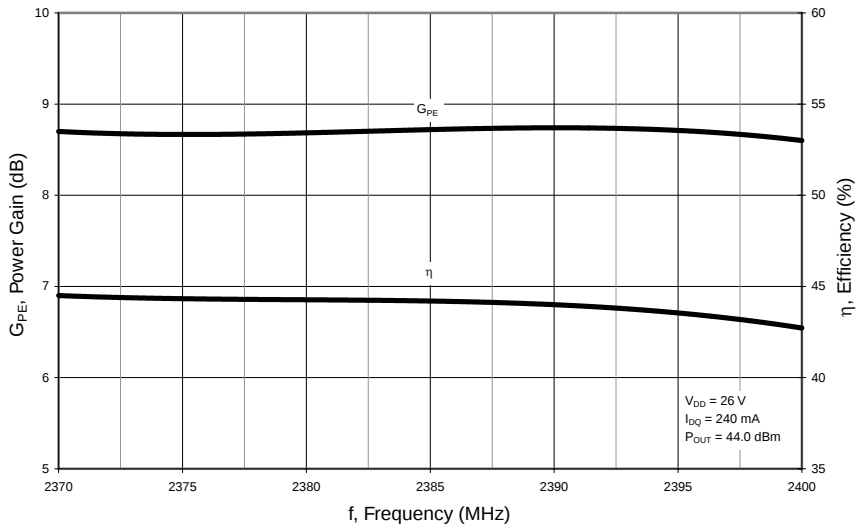
Intermodulation Distortion vs Output Power



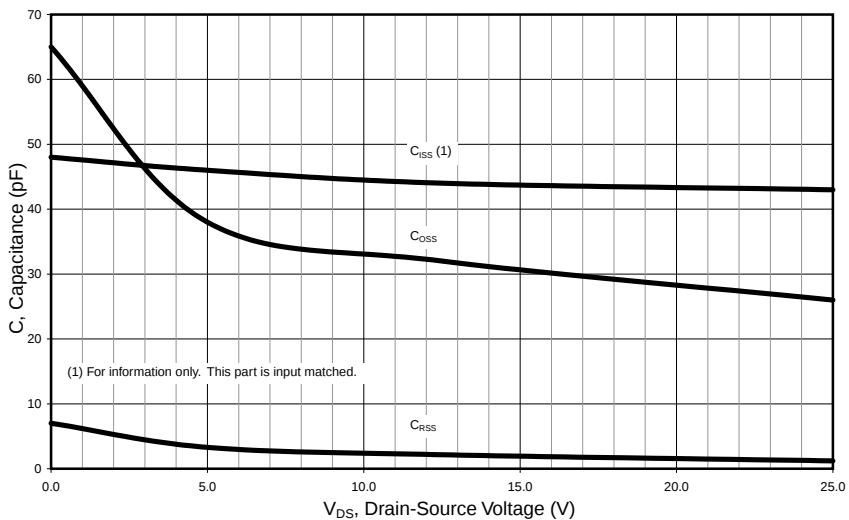
Power Gain & Efficiency vs Output Power



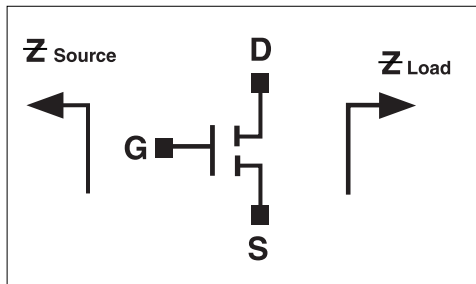
Power Gain and Efficiency vs Frequency



Capacitance vs Drain Voltage



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$$V_{DD} = 26.5V$$

$$I_{DQ} = 260mA$$

Frequency (MHz)	Z Source	Z Load
2340	1.54 - j3.80	.89 - j2.23
2350	1.54 - j3.79	.89 - j2.21
2360	1.54 - j3.77	.89 - j2.19
2370	1.54 - j3.75	.90 - j2.17
2380	1.53 - j3.73	.90 - j2.15
2390	1.53 - j3.69	.90 - j2.13
2400	1.53 - j3.69	.90 - j2.11
2410	1.52 - j3.67	.90 - j2.09
2420	1.52 - j3.65	.91 - j2.07
2430	1.52 - j3.63	.91 - j2.05
2440	1.51 - j3.62	.91 - j2.03

DC Safe Operating Area

